Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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CNB1302

Reflective Photosensor

■ Overview

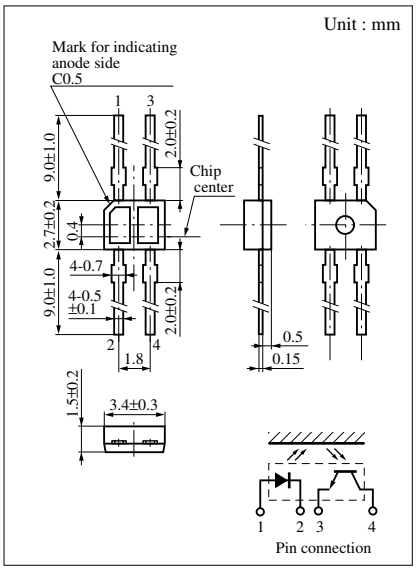
CNB1302 is a small, thin reflective photosensor consisting of a high efficiency GaAs infrared light emitting diode which is integrated with a high sensitivity Si phototransistor in a single resin package.

■ Features

- Ultraminiature, thin type : 2.7 × 3.4 mm (height : 1.5 mm)
- Visible light cutoff resin is used
- Fast response : t_r, t_f = 20µs (typ.)
- Easy interface for control circuit

■ Applications

- Control of motor and other rotary units
- Detection of position and edge
- Detection of paper, film and cloth
- Start, end mark detection of magnetic tape



■ Absolute Maximum Ratings (Ta = 25˚C)

Parameter		Symbol	Ratings	Unit
Input (Light emitting diode)	Reverse voltage (DC)	V_R	3	V
	Forward current (DC)	I_F	50	mA
	Power dissipation	P_D *1	75	mW
Output (Photo transistor)	Collector current	I_C	20	mA
	Collector to emitter voltage	V_{CEO}	30	V
	Emitter to collector voltage	V_{ECO}	5	V
	Collector power dissipation	P_C *2	50	mW
Temperature	Operating ambient temperature	T_{opr}	–25 to +85	˚C
	Storage temperature	T_{stg}	–30 to +100	˚C

*1 Input power derating ratio is 1.0 mW/˚C at Ta ≥ 25˚C.

*2 Output power derating ratio is 0.67 mW/˚C at Ta ≥ 25˚C.

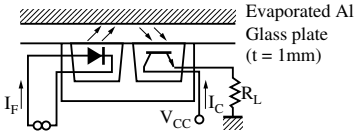
■ Electrical Characteristics (Ta = 25˚C)

Paramwter		Symbol	Conditions	min	typ	max	Unit
Input characteristics	Forward voltage (DC)	V_F	I_F = 50mA		1.3	1.5	V
	Reverse current (DC)	I_R	V_R = 3V		0.01	10	µA
	Capacitance between terminals	C_t	V_R = 0V, f = 1MHz		30		pF
Output characteristics	Collector cutoff current	I_{CEO}	V_{CE} = 10V			200	nA
Transfer characteristics	Collector current	I_C *1, *2	V_{CC} = 5V, I_F = 10mA, R_L = 100Ω, d = 1mm	90		880	µA
	Leakage current	I_D	V_{CC} = 5V, I_F = 10mA, R_L = 100Ω			200	nA
	Response time	t_r *3 , t_f *4	V_{CC} = 5V, I_C = 0.1mA, R_L = 100Ω		20		µs
	Collector to emitter saturation voltage	$V_{CE(sat)}$	I_F = 20mA, I_C = 0.1mA			0.4	V

*1 I_C classifications

Class	Q	R	S
I_C (µA)	90 to 220	180 to 440	360 to 880

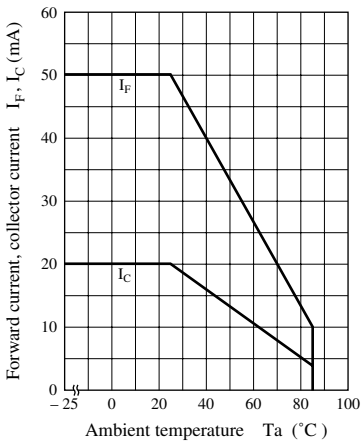
*2 Output current measurement method



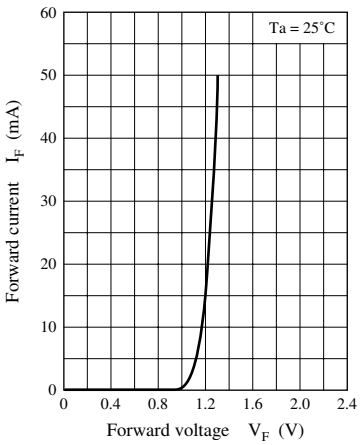
*3 Time required for the output current to increase from 10% to 90% of its final value

*4 Time required for the output current to decrease from 90% to 10% of its initial value

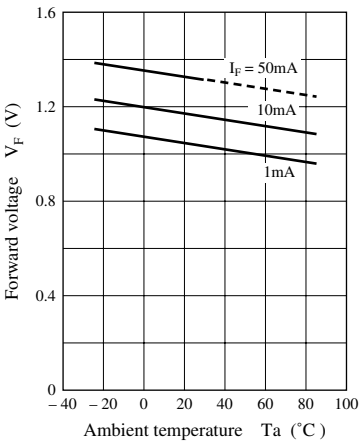
I_F , I_C — Ta



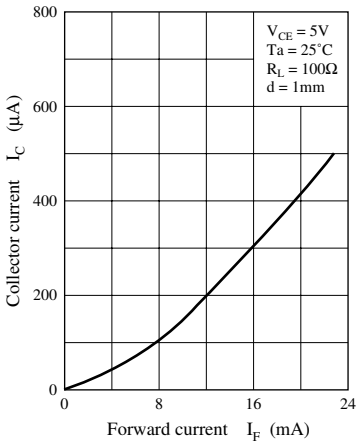
I_F — V_F



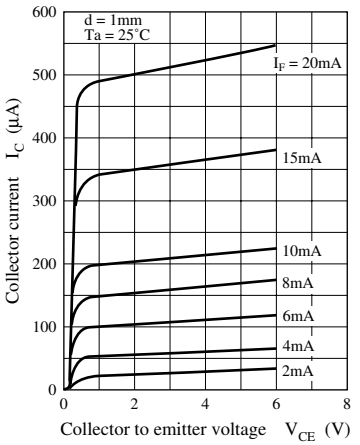
V_F — Ta



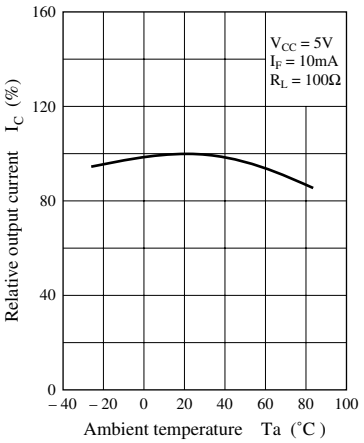
I_C — I_F



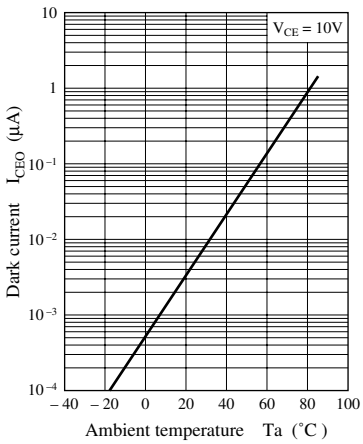
I_C — V_{CE}



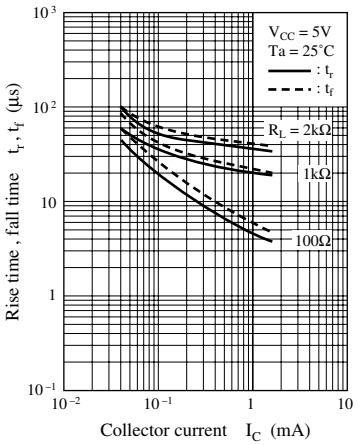
I_C — Ta



I_{CEO} — Ta



t_r , t_f — I_C



I_C — d